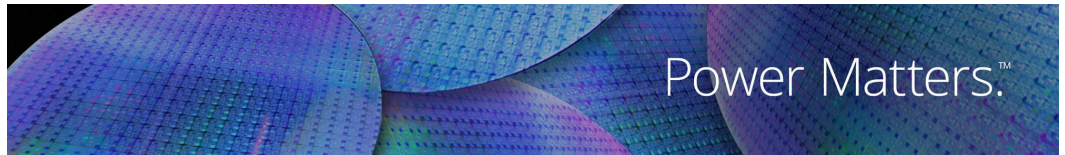


## POWER DISCRETES & MODULES

- ▶ Silicon Carbide (SiC)
- ▶ Diode and Rectifier Devices
- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
  - BJT Modules (Power Integrated Circuit, PIC)
  - Darlington Transistors
  - Darlington Transistor Array
  - NPN PNP Complimentary Transistor
  - **NPN Transistor**
  - PNP Transistor
- ▶ Legacy Power Discretets & Modules



[Home](#) / [Power Discretets & Modules](#) / [BJT \(BiPolar Junction Transistor\)](#) / [NPN Transistor](#) / [JAN2N2857 \(#76564\)](#)

# JAN2N2857 (#76564)

**Product Status**

■ In Production

[Overview](#)   [Resources](#)   [Diagrams](#)   [Ordering](#)   [Support](#)

The 2N2857 is a military qualified silicon NPN transistor (also available in commercial version), designed for UHF equipment and other high-reliability applications. Common applications include low noise amplifier, oscillator, and mixer applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.

Package      ESD Bag

Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V
Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	$I_C$			0.04	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			15	V
Junction Temperature (°C)	$T_J$	-65		200	°C
Junction Temperature (°C)	$T_J$	-65		200	°C
Power Dissipation	$P_D$			0.2	W
Thermal Resistance, Junction to Ambient (°C/W)	$R_{\theta JA}$			400	°C/W

This part can be found in the following product categories:

- [Power Discretets & Modules](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [NPN Transistor](#)